

Sikandar Aftab

List of Publications by Year in descending order

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Version: 2024-02-01

30
papers

698
citations

394286

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all docs

31
docs citations

31
times ranked

627
citing authors

#	ARTICLE	IF	CITATIONS
1	Investigation of magnetron sputtered Ni@Cu/ WS ₂ as an electrode material for potential supercapattery devices. International Journal of Energy Research, 2022, 46, 7334-7347.	2.2	8
2	Platinum Disulfide (PtS ₂) and Silicon Pyramids: Efficient 2D/3D Heterojunction Tunneling and Breakdown Diodes. ACS Applied Electronic Materials, 2022, 4, 917-924.	2.0	12
3	Highly stable binary composite of nickel silver sulfide (NiAg ₂ S) synthesized using the hydrothermal approach for high-performance supercapattery applications. International Journal of Energy Research, 2022, 46, 11346-11358.	2.2	37
4	Flexible Diodes with Low Breakdown Voltage for Steep Slope Transistors and One Diodeâ€One Resistor Applications. Advanced Electronic Materials, 2022, 8, .	2.6	8
5	Lateral PIN (p-MoTe ₂ /Intrinsic-MoTe ₂ /n-MoTe ₂) Homojunction Photodiodes. ACS Applied Nano Materials, 2022, 5, 6455-6462.	2.4	19
6	Single nanoflake-based PtSe ₂ p-n junction (in-plane) formed by optical excitation of point defects in BN for ultrafast switching photodiodes. Journal of Materials Chemistry C, 2021, 9, 199-207.	2.7	23
7	NIR self-powered photodetection and gate tunable rectification behavior in 2D GeSe/MoSe ₂ heterojunction diode. Scientific Reports, 2021, 11, 3688.	1.6	34
8	A reversible and stable doping technique to invert the carrier polarity of MoTe ₂ . Nanotechnology, 2021, 32, 285701.	1.3	21
9	Effect of an optimal oxide layer on the efficiency of graphene-silicon Schottky junction solar cell. International Journal of Energy Research, 2021, 45, 18173-18181.	2.2	4
10	Enhanced electrochemical performance of battery-grade cobalt phosphate via magnetron sputtered copper interfacial layer for potential supercapattery applications. International Journal of Energy Research, 2021, 45, 18658-18669.	2.2	14
11	Synergistic effect of magnetron sputtered silver nano-islands and Co ₃ (PO ₄) ₂ for high performance supercapattery devices. Journal of Electroanalytical Chemistry, 2021, 898, 115612.	1.9	11
12	Self-biased photovoltaic behavior in van der Waals MoTe ₂ /MoSe ₂ heterostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2021, 134, 114912.	1.3	3
13	ReSe ₂ /metal interface for hydrogen gas sensing. Journal of Colloid and Interface Science, 2021, 603, 511-517.	5.0	12
14	Switching photodiodes based on (2D/3D) PdSe ₂ /Si heterojunctions with a broadband spectral response. Journal of Materials Chemistry C, 2021, 9, 3998-4007.	2.7	24
15	High mobility ReSe ₂ field effect transistors: Schottky-barrier-height-dependent photoresponsivity and broadband light detection with Co decoration. 2D Materials, 2020, 7, 015010.	2.0	36
16	A facile route to enhance the mobility of MoTe ₂ field effect transistor via chemical doping. Superlattices and Microstructures, 2020, 147, 106698.	1.4	22
17	WSe ₂ Homo Junction p-n Diode Formed by Photoinduced Activation of Mid-Gap Defect States in Boron Nitride. ACS Applied Materials & Interfaces, 2020, 12, 42007-42015.	4.0	34
18	Van der Waals Multi-Heterostructures (PN, PIN, and NPN) for Dynamic Rectification in 2D Materials. Advanced Materials Interfaces, 2020, 7, 2001479.	1.9	24

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19	Carrier polarity modulation of molybdenum ditelluride (MoTe ₂) for phototransistor and switching photodiode applications. <i>Nanoscale</i> , 2020, 12, 15687-15696.	2.8	26
20	Asymmetric electrode incorporated 2D GeSe for self-biased and efficient photodetection. <i>Scientific Reports</i> , 2020, 10, 9374.	1.6	38
21	Two-dimensional electronic devices modulated by the activation of donor-like states in boron nitride. <i>Nanoscale</i> , 2020, 12, 18171-18179.	2.8	28
22	An effectual enhancement to the electrical conductivity of graphene FET by silver nanoparticles. <i>Diamond and Related Materials</i> , 2020, 106, 107833.	1.8	10
23	Gate dependent phonon shift in tungsten disulfide (WS ₂) field effect transistor. <i>Materials Research Express</i> , 2019, 6, 115909.	0.8	11
24	Thickness-dependent resistive switching in black phosphorus CBRAM. <i>Journal of Materials Chemistry C</i> , 2019, 7, 725-732.	2.7	51
25	MoTe ₂ van der Waals homojunction p-n diode with low resistance metal contacts. <i>Nanoscale</i> , 2019, 11, 9518-9525.	2.8	54
26	Formation of an MoTe ₂ based Schottky junction employing ultra-low and high resistive metal contacts. <i>RSC Advances</i> , 2019, 9, 10017-10023.	1.7	27
27	Gate Modulation of the Spin-orbit Interaction in Bilayer Graphene Encapsulated by WS ₂ films. <i>Scientific Reports</i> , 2018, 8, 3412.	1.6	20
28	Van der Waals heterojunction diode composed of WS ₂ flake placed on p-type Si substrate. <i>Nanotechnology</i> , 2018, 29, 045201.	1.3	21
29	Comparison of Electrical and Photoelectrical Properties of ReS ₂ Field-Effect Transistors on Different Dielectric Substrates. <i>ACS Applied Materials & Interfaces</i> , 2018, 10, 32501-32509.	4.0	44
30	Gate Tunable Transport in Graphene/MoS ₂ /(Cr/Au) Vertical Field-Effect Transistors. <i>Nanomaterials</i> , 2018, 8, 14.	1.9	22